

/ Descriptions

WR0<50 P M M E QSQ æ M y s ll 1 Silicon NPN transistor in a TO-92LM Plastic Package.

/ Features

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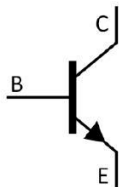
High Collector-Base Voltage, high Current Gain Bandwidth Product.

/ Applications

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High voltage power amplifier.

/ Equivalent Circuit



/ Pinning



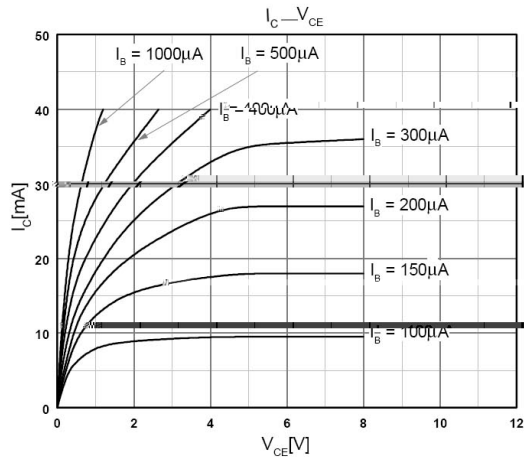
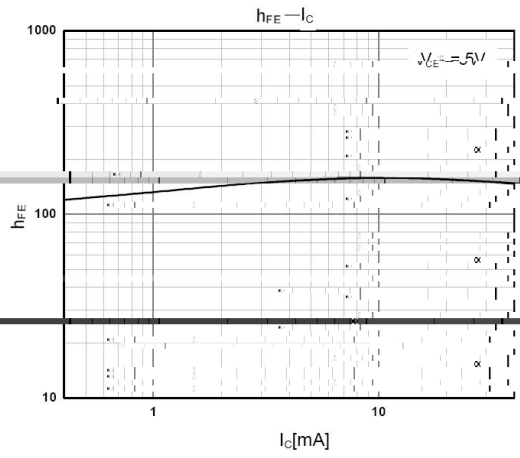
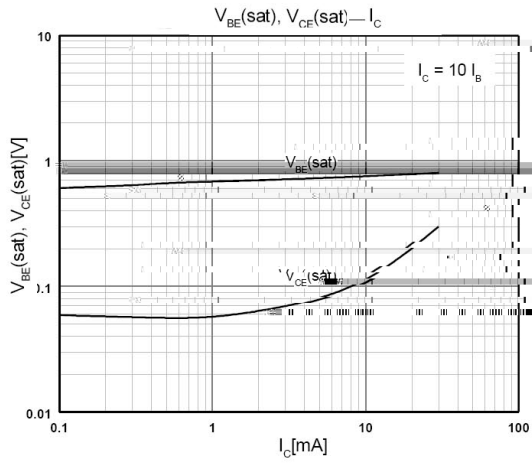
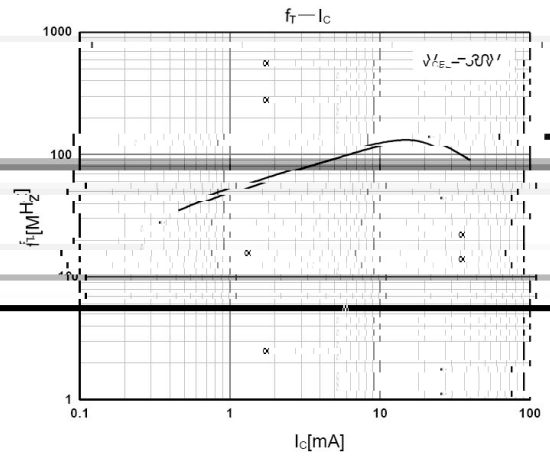
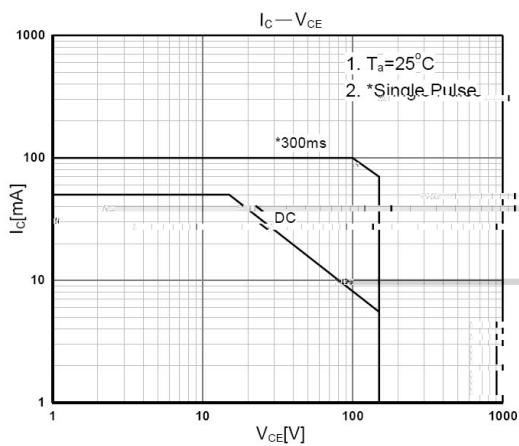
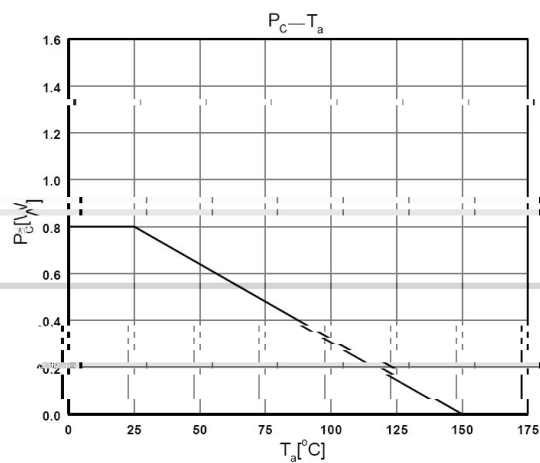
PIN1 $\times$ Base PIN 2 $\times$ Collector PIN 3 $\times$ Emitter

/ h_{FE} Classifications & Marking

h _{FE} Classifications Symbol	R	O	Y
h _{FE} Range	40 80	70 140	120 240

Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	200	V
Collector to Emitter Voltage	V_{CEO}	150	V
Emitter to Base Voltage	V_{EBO}	5.0	V
Collector Current (DC)	I_C	50	mA
Collector Power Dissipation	P_C	1800	mW

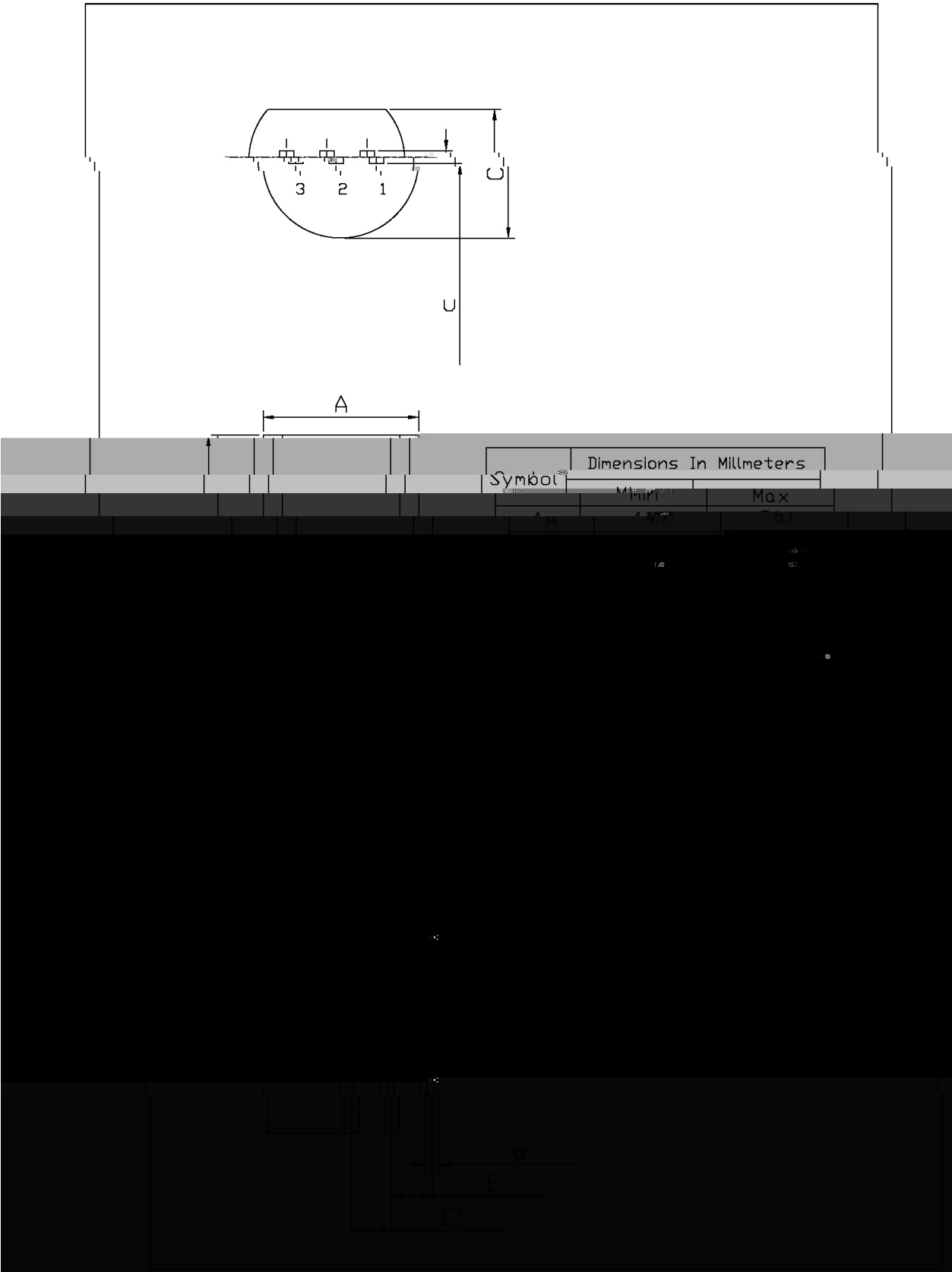
/ Electrical Characteristic Curve



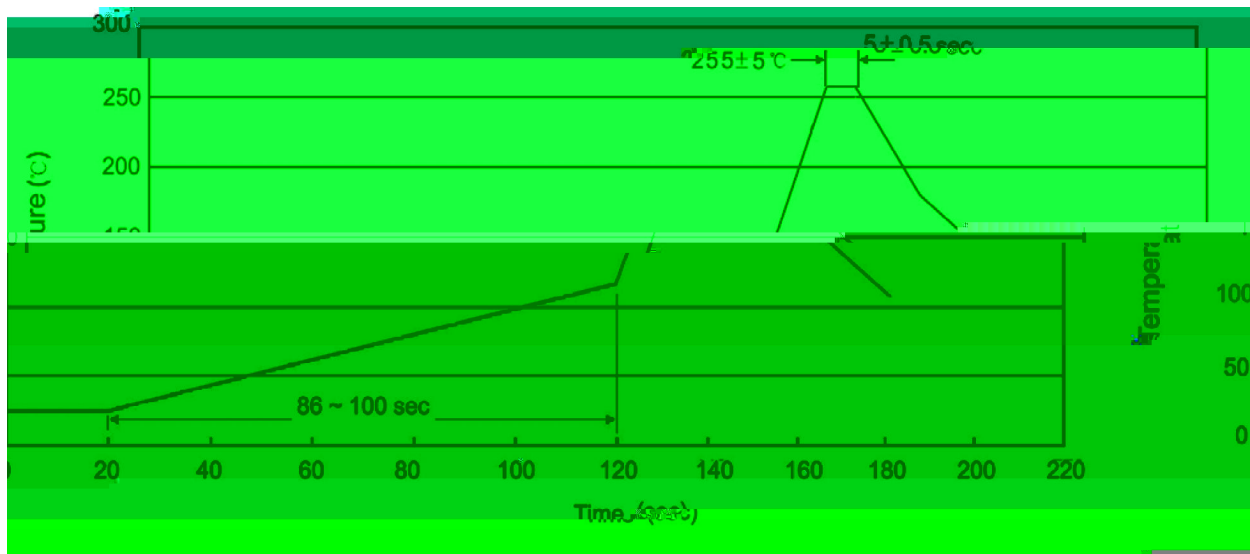
/ Package Dimensions

TO-92LM

Unit: mm



() / Temperature Profile for Dip Soldering(Pb-Free)



说明

1. 预加热: 25~150℃, 时间: 60~90sec;
2. 峰值温度: 255±5℃, 持续时间: 5~0.5sec;
3. 冷却速度: 2~10℃/sec.

Note:

1. Preheating: 25~150℃, Time: 60~90sec.
2. Peak Temp.: 255±5℃, Duration: 5~0.5sec.
3. Cooling Speed: 2~10℃/sec.

/ Resistance to Soldering Heat Test Conditions

温度: 270±5℃, 时间: 10±1 sec. Temp.: 270±5℃ Time: 10±1 sec

/ Packaging SPEC.

散装 / BULK

Package Type 封装形式	Units 包装数量					Dimension 包装尺寸 (unit: mm3)		
	只袋	袋盒	只盒	盒箱	只箱	袋	盒	箱

纸带 / AMMO

Package Type 封装形式	Units 包装数量					Dimension 包装尺寸 (unit: mm3)	
	只纸带	纸带盒	纸带层盒	盒箱	只箱	盒	箱
							小箱 大箱

/ Notices